Product data sheet

1. General description

High voltage, high speed, planar passivated NPN power switching transistor in a SOT54 (TO92) plastic package intended for use in low power SMPS emitter switching circuits.

2. Features and benefits

- Fast switching
- · High base current drive capability
- High voltage capability
- Very low switching and conduction losses

3. Applications

- Emitter-switched low power SMPS circuits
- Self Oscillating Power Supplies
- AC-DC converters
- DC-AC inverters

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _C	collector current	DC		-	-	1	Α
P _{tot}	total power dissipation	T _{lead} ≤ 25 °C; <u>Fig. 1</u>		-	-	2	W
T _j	junction temperature			-	-	150	°C
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0 V		-	-	700	V
Static characteristics							
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA}; T_{lead} = 25 ^{\circ}\text{C};$ Fig. 5; Fig. 6		12	22	32	
		V_{CE} = 5 V; I_{C} = 100 mA; T_{lead} = 25 °C; Fig. 5; Fig. 6		14	24	34	
		V_{CE} = 5 V; I_{C} = 0.75 A; T_{lead} = 25 °C; Fig. 5; Fig. 6		12	15.5	20	





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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter		C
2	С	collector		В
3	В	base		- / -
			3 2 1 TO-92 (SOT54)	sym123

6. Ordering information

Table 3. Ordering information

Type number	Package						
	Name	Description	Version				
TB100	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54				

7. Marking

Table 4. Marking codes

Type number	Marking code
TB100	TB100

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CESM}	collector-emitter peak voltage	V _{BE} = 0 V	-	700	V
V_{CBO}	collector-base voltage	I _E = 0 A	-	700	V
I _C	collector current	DC	-	1	Α
I _{CM}	peak collector current		-	2	Α
I _B	base current		-	0.5	Α
I _{BM}	peak base current		-	3	Α
P _{tot}	total power dissipation	T _{lead} ≤ 25 °C; <u>Fig. 1</u>	-	2	W
T _{stg}	storage temperature		-65	150	°C
Tj	junction temperature		-	150	°C

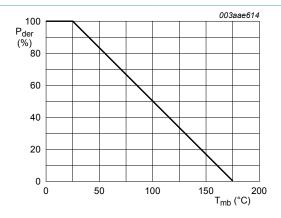


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

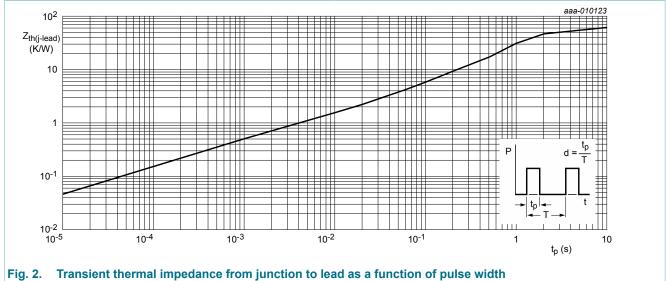
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\,\%$$

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-lead)}	thermal resistance from junction to lead		-	-	60	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	printed circuit board mounted; lead length = 4 mm; Fig. 2	-	150	-	K/W



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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		'			
I _{CES}	collector-emitter cut-off	V _{BE} = 0 V; V _{CE} = 700 V; T _{lead} = 25 °C	-	0.8	100	μA
	current	V _{BE} = 0 V; V _{CE} = 700 V; T _j = 125 °C	-	2	500	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = 9 V; I _C = 0 A; T _{lead} = 25 °C	-	0.05	100	μΑ
V _{CEsat}	collector-emitter saturation voltage	$I_C = 0.75 \text{ A}$; $I_B = 0.15 \text{ A}$; $T_{lead} = 25 ^{\circ}\text{C}$; Fig. 3	-	0.24	1	V
V_{BEsat}	base-emitter saturation voltage	$I_C = 0.75 \text{ A}; I_B = 0.15 \text{ A}; T_{lead} = 25 ^{\circ}\text{C};$ Fig. 4	-	0.93	1.3	V
h _{FE}	DC current gain	I _C = 10 mA; V _{CE} = 5 V; T _{lead} = 25 °C; Fig. 5; Fig. 6	12	22	32	
		I_C = 100 mA; V_{CE} = 5 V; T_{lead} = 25 °C; Fig. 5; Fig. 6	14	24	34	
		I _C = 0.75 A; V _{CE} = 5 V; T _{lead} = 25 °C; Fig. 5; Fig. 6	12	15.5	20	
Dynamic ch	naracteristics (resistive loa	d)		,		,
t _s	storage time	I _C = 1 A; I _{Bon} = 0.2 A; I _{Boff} = -0.2 A;	-	2	-	μs
t _f	fall time	$R_L = 75 \Omega$; $V_{BB} = -4 V$; $T_{lead} = 25 °C$; Fig. 7; Fig. 8	-	320	-	ns

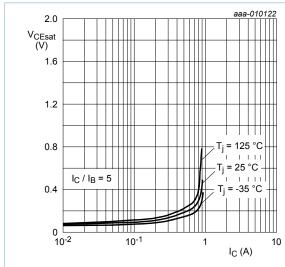


Fig. 3. Collector-emitter saturation voltage as a function of collector current; typical values

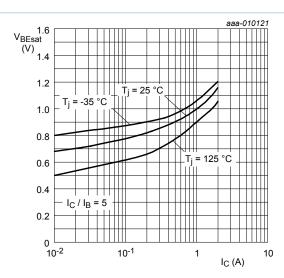


Fig. 4. Base-emitter saturation voltage as a function of collector current; typical values

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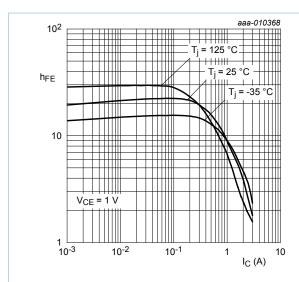


Fig. 5. DC current gain as a function of collector current; typical values

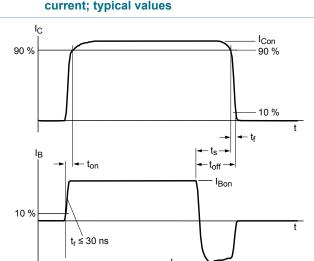


Fig. 7. Switching times waveforms for resistive load

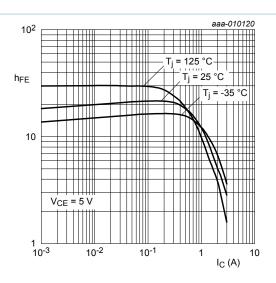


Fig. 6. DC current gain as a function of collector current; typical values

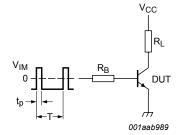


Fig. 8. Test circuit for resistive load switching

$$\begin{split} V_{IM} = & -6 \text{ to } + 8 \text{ V; } V_{CC} = 250 \text{ V; } t_p = 20 \text{ μs; } \pmb{\delta} = \frac{t_p}{T} = 0.01 \\ R_B \text{ and } R_L \text{ calculated from } I_{Con} \text{ and } I_{Bon} \text{ requirements.} \end{split}$$

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11. Package outline

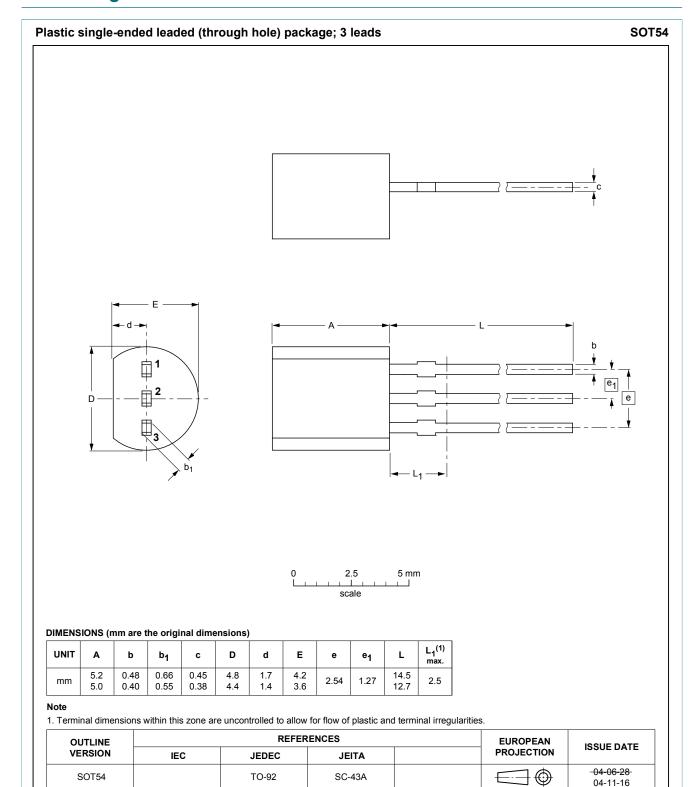


Fig. 9. Package outline TO-92 (SOT54)

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